



Absorptive and Reflective 2-4GHz Coaxial SP8T



Features

- Wide Band Operation 2-4GHz
- High Power Handle Capability up to 30W upon request.
- TTL compatible driver include
- Fast Switching Speed
- Low Insertion Loss and High Isolation
- Temperature Range -40°C~+85°C
- Customization available upon request

Absorptive SP8T- Single Pole Eight Throw						
Part Number	Frequency (GHz)	Insert. Loss (dB)	VSWR (Max:1)	Isolation min (dB)	Power (Watts)	Switching Speed (ns)
RFSP8TA0204G	2-4	2.0	1.5	80	P1dB=1W min 1W PK <200us	80
Reflective SP8T- Single Pole Eight Throw						
Part Number	Frequency (GHz)	Insert. Loss (dB)	VSWR (Max:1)	Isolation min (dB)	Power (Watts)	Switching Speed (ns)
RFSP8TR0204G	2-4	1.6	1.5	80	1W~5W	80

Electrical Operation

DC Biasing:
+5.0V (300mA max.)
-5.0V (30mA max.)
High Voltage Biasing is required for high RF power model.

Mechanical Specification

Case Style: As shown
Finishing: Gold plating for brass material
Other finishing available
Connector: SMA-F Per MIL-C-39012
Seal: Hermetically Sealed
Control PIN: 0.02" dia x 0.15" solder pins
Weight: 40 grams max.

Connector:

Micro-D 9 Pin Female

PIN 1: +5V
PIN 2: -5V
PIN 3: GND
PIN 4: C1
PIN 5: C2
PIN 6: C3
PIN 7, 8, 9 N/A

TTL Logic Control:

C3	C2	C1	
0	0	0	J0→J1
0	0	1	J0→J2
0	1	0	J0→J3
0	1	1	J0→J4
1	0	0	J0→J5
1	0	1	J0→J6
1	1	0	J0→J7
1	1	1	J0→J8

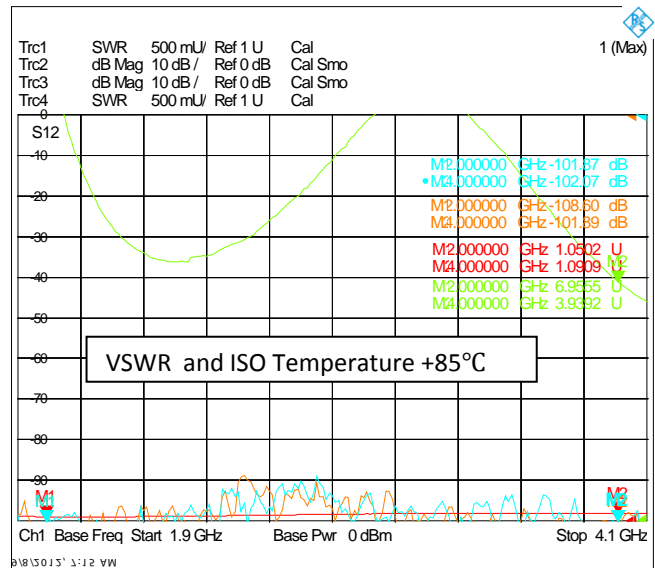
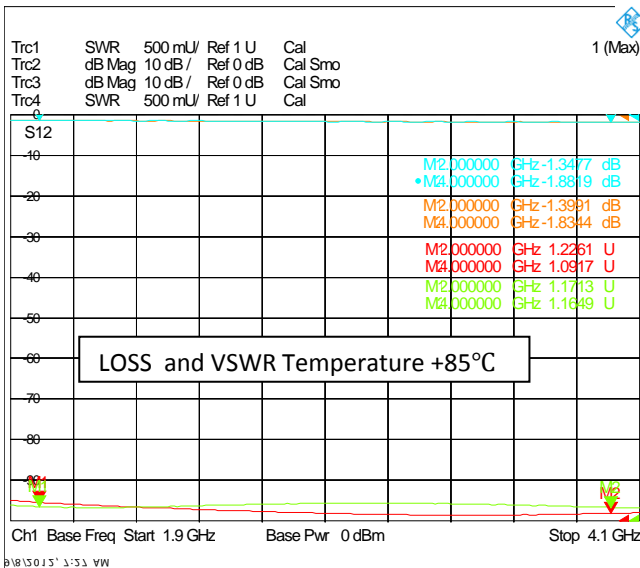
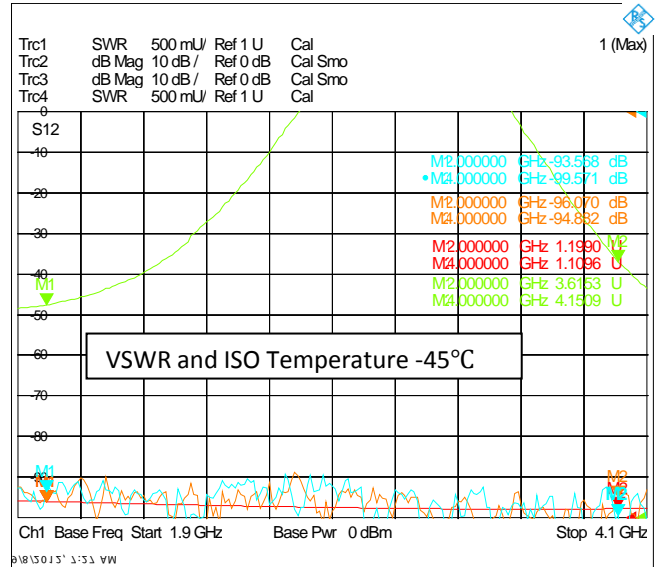
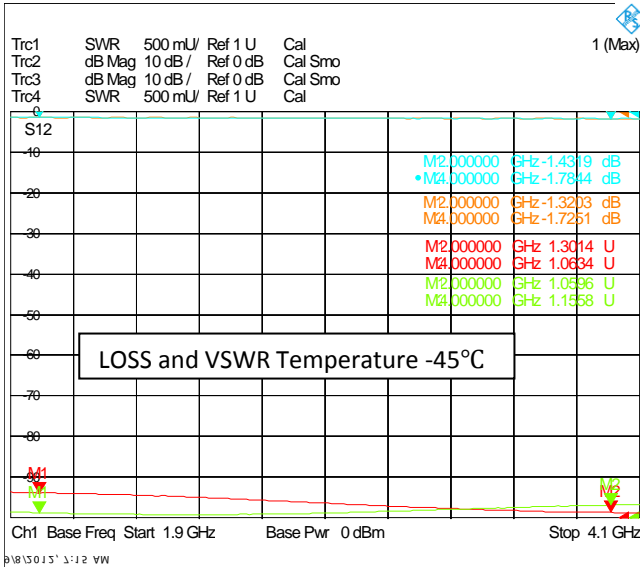
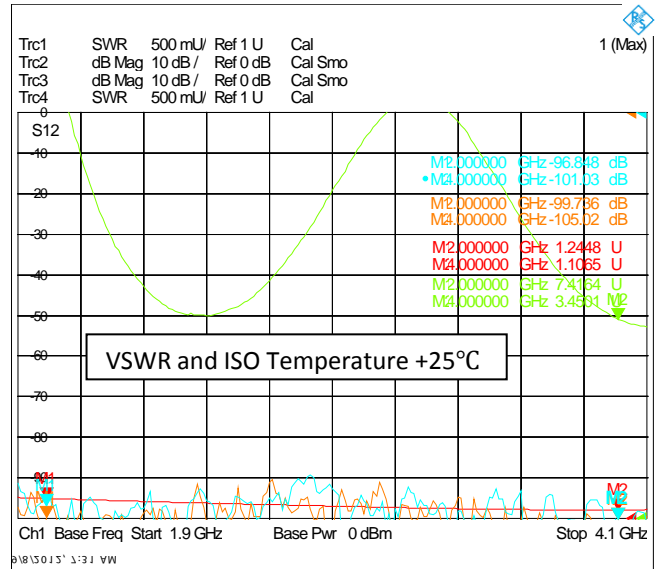
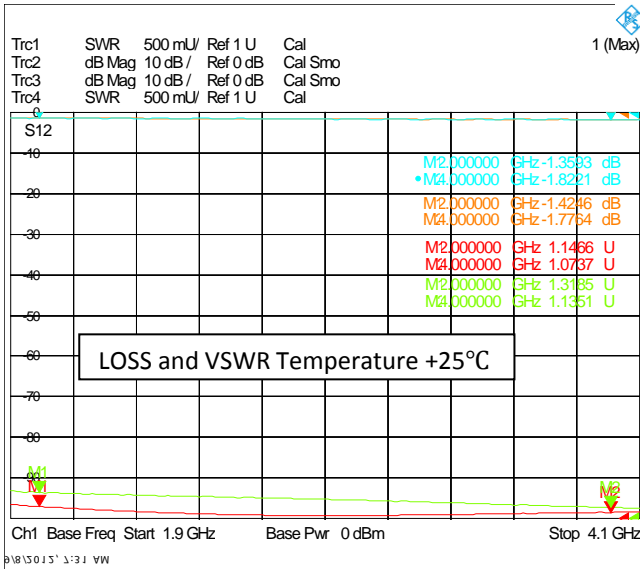


RF-LAMBDA

The power beyond expectations

2~4GHz PIN SP8T

Absorptive / Reflective Coaxial Single Pole Eight Throw Switch 2-4GHz

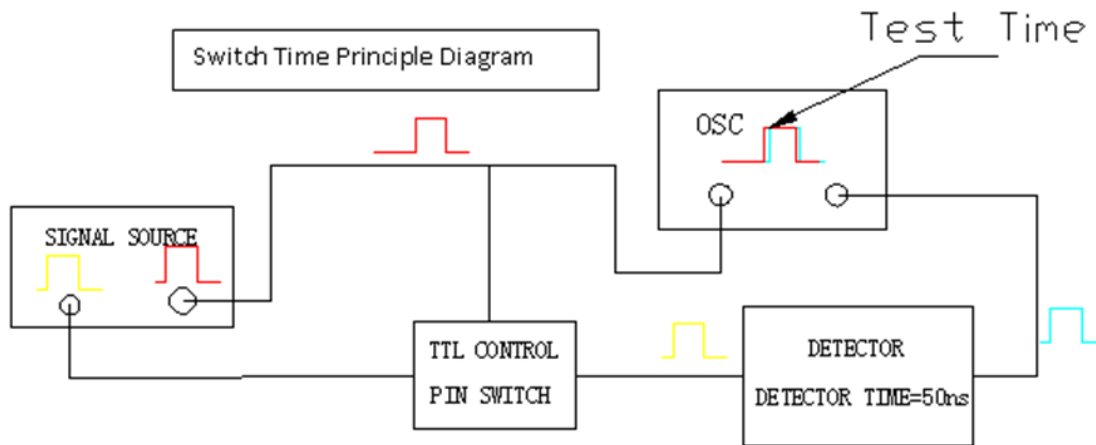




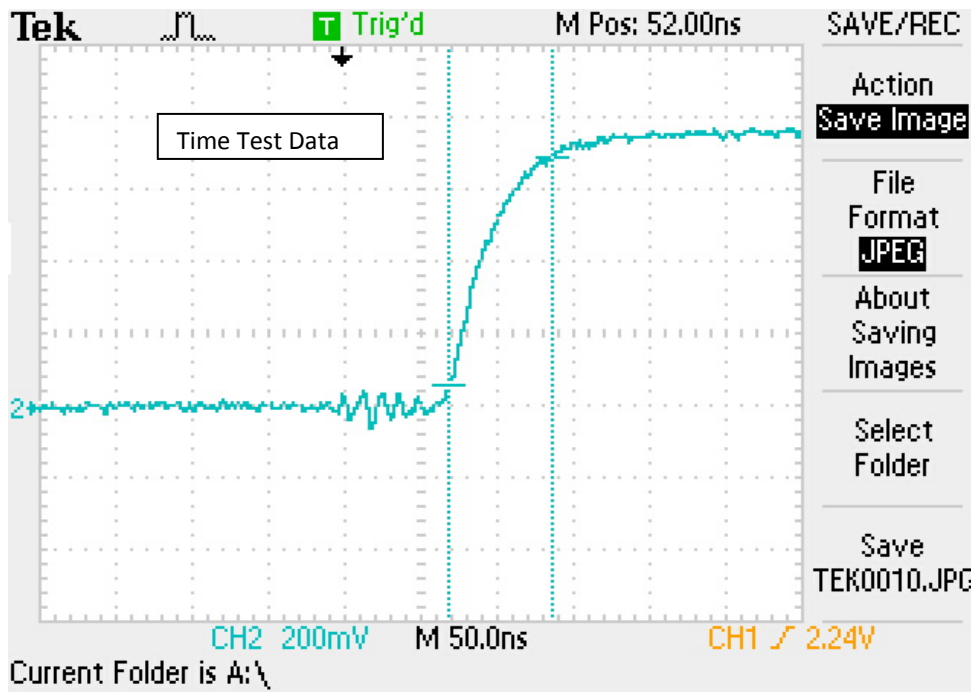
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The power beyond expectations

2~4GHz PIN SP8T



$$\text{Switch Time} = \text{Test Time} - \text{Detector Time}$$



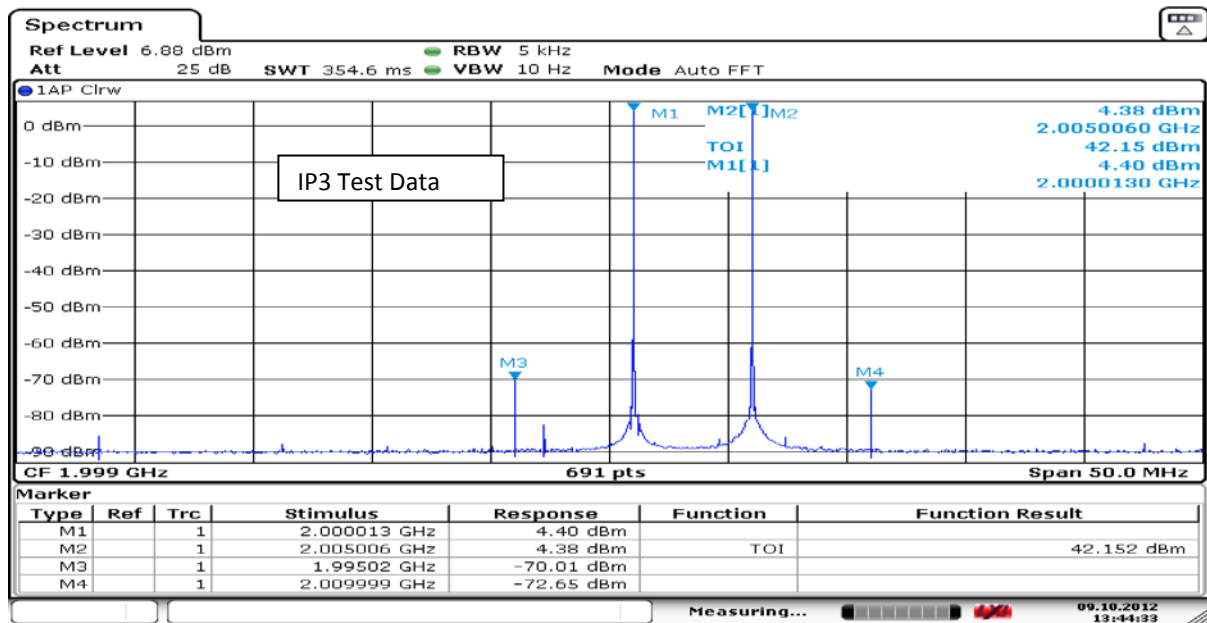


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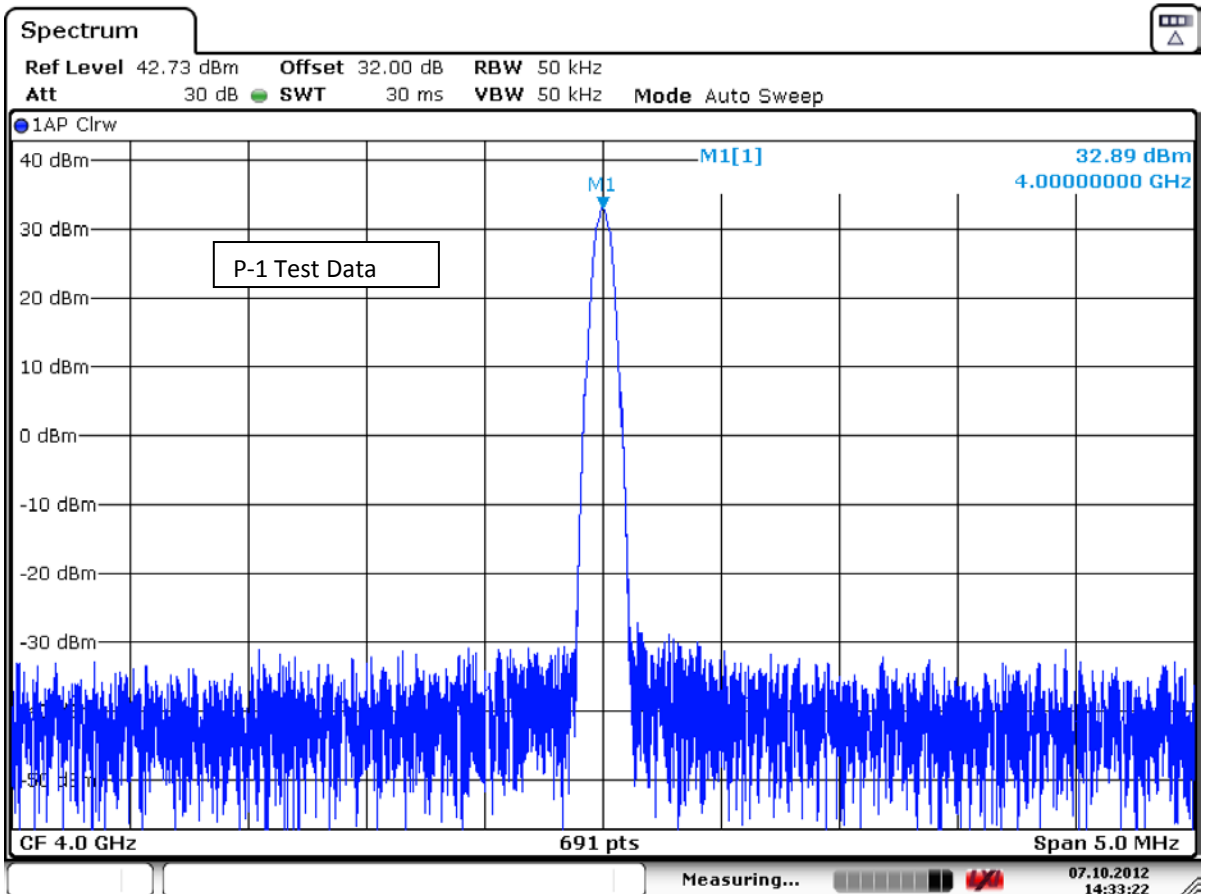
The power beyond expectations

2~4GHz PIN SP8T

Absorptive / Reflective Coaxial Single Pole Eight Throw Switch 2-4GHz



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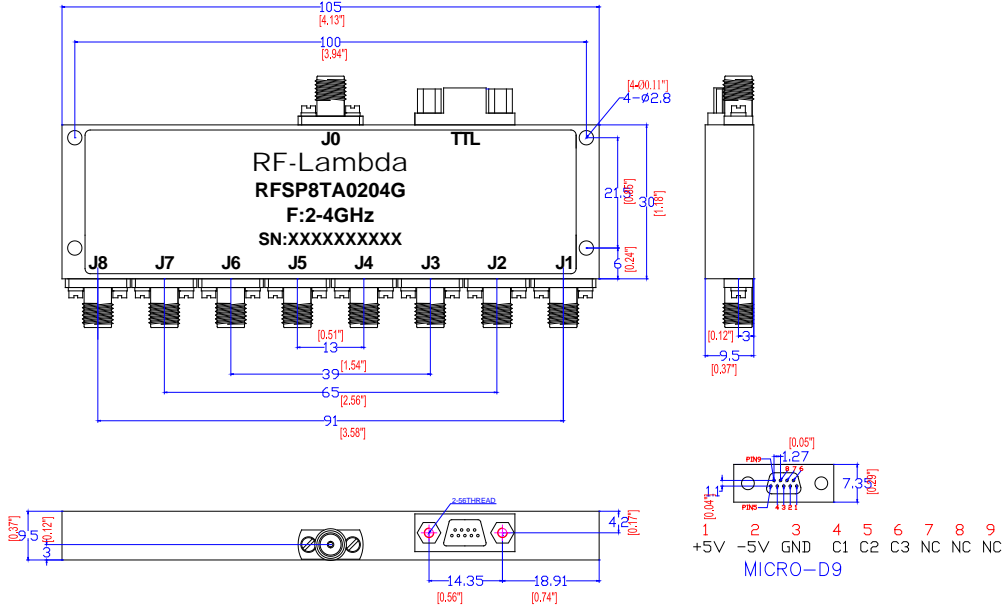


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Outline Drawing:

All Dimensions in mm



Note: Contact RF-Lambda for faster switching speed, higher power handle, higher isolation

1. Higher power handle capability will give lower isolation , higher biasing current and slower switching speed.
2. Narrower frequency band will improve insertion loss and isolation.